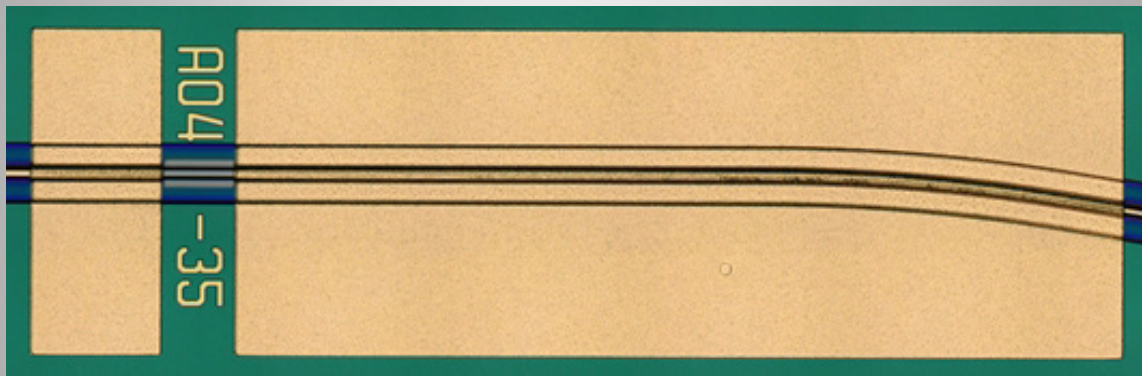




AT A GLANCE

High power o-band
InP BH DFB



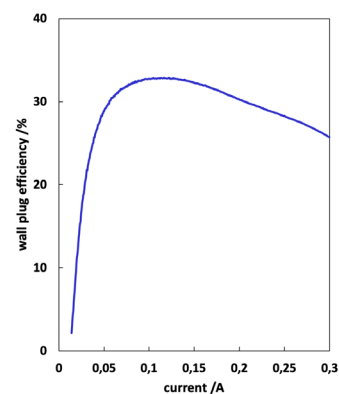
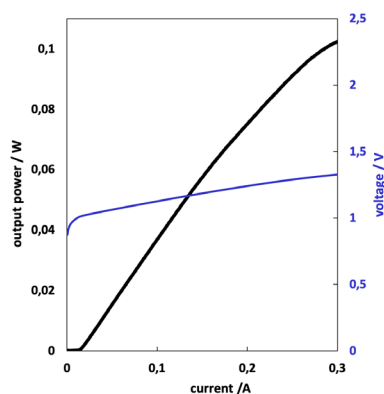
Features

- DFB plus SOA approach
- Optional integration of monitor diode
- p-side up or flip-chip configuration
- integrated taper for low loss optical coupling
- 9° output facet
- on request precise alignment structures for lateral & vertical positioning
- flexible adaptation of devices corresponding to customer's applications: e.g. center wavelength, coating against $n=1.5...$

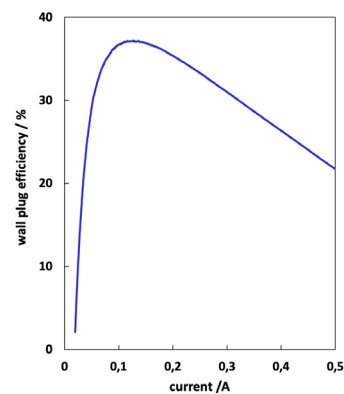
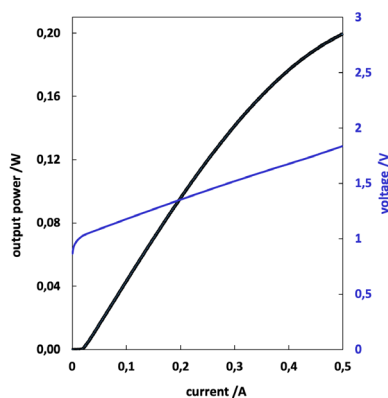
Applications

- Telecom/Datacom
- Sensors

Array DFB (20°C, p-side up mounted)



Single DFB (20°C, p-side down mounted)



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Parameters	Min	Typ	Max	Unit
Side mode suppression ratio		40		dB
Relative intensity noise	-155	-145		dB/Hz
Optical line width (Lorentzian)			1.0	MHz
Far field angle (FWHM)		16x22		°